UT54BS16210

Features

- 3.3V operating power supply with typical 11Ω switch connection between ports
- 5.0V operating power supply with typical 5Ω switch connection between ports
- · Bidirectional operation
- Ultra-low power CMOS technology
- ESD Rating HBM: 2000V, Class 2
- Signal Isolation: -60dB
- Channel Bandwidth (3dB): 500MHz
- Standard Microcircuit Drawing (SMD):
 - 5962-15245
 - QML Q and V compliant part
- Package Options: 48-Lead Flatpack

Operational Environment

- Temperature Range: -55°C to +125°C
- Total Dose: 300 krad(Si)
- SEL Immune: ≤100 MeV-cm²/mg

Applications

- Memory Interface
- Bus Isolation
- Redundancy
- Supports Analog Applications

Introduction

The UT54BS16210 provides 20 bits of high-speed CMOS-compatible bus switching. The low on-state resistance of the switch allows connections to be made with minimal propagation delay. The device is organized as a dual 10-bit bus switch with separate output-enable (/EN) inputs. It can be used as two 10-bit bus switches or as one 20-bit bus switch. When output enable (/EN) is low, the associated 10-bit bus switch is on and port A is connected to port B. When /EN is high, the switch is open and a high-impedance state exists between the two ports.



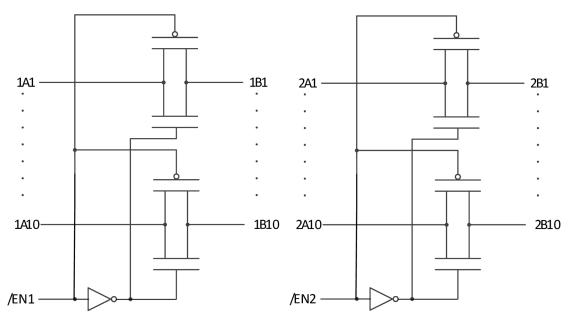


Figure 1: 20-bit Bus Switch Block Diagram

Pinlist

TO = TTL Output

TTB = Three-State TTL Bidirectional

CI = CMOS Input

TUI = TTL Input (Internally Pulled High)

TI = TTL Input

TTO = Three-State TTL Output
DIO = Differential Input/Output

Table 1: Pinlist

Number	Name	Description
2, 3, 4, 5, 6, 7, 9, 10, 11, 12, 13, 14, 16, 18, 19, 20, 21, 22, 23, 24	nAn	Port A Pins
25, 26, 27, 28, 29, 30, 31, 33, 34, 35, 36, 37, 38, 39, 40, 42, 43, 44, 45, 46	nBn	Port B pins
47, 48	/ENn	Active LOW enable pin
8, 17, 32, 41	V _{SS}	Ground Pin
15	V_{DD}	Supply Pin, +3.3V -or- +5.0V
1	NC	No Connect (electrically not connected to die)



Package Pinout Diagram

			ı	
NC	1		48	/1EN
1A6	2	<u> </u>	47	/2EN
1A7	3		46	1B10
1A8	4		45	1B10 1B9
1A9	5		44	1B3
1A10	6		43	1B7
1A5	7		42	1B7 1B6
VSS	8		41	VSS
1A4	9		40	1B5
1A3	10	U	39	1B3
1A2	11	T54BS162	38	1B3
1A1	12	4B	37	1B3
2A1	13	S	36	1B2 1B1
2A2	14	62	35	2B1
VDD	15	210	34	2B2
2A3	16		33	2B3
VSS	17		32	VSS
2A4	18		31	2B4
2A5	19		30	2B5
2A6	20		29	2B10
2A7	21		28	2B9
2A8	22		27	2B3
2A9	23		26	2B7
2A10	24		25	2B6
2/110				200



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Absolute Maximum Ratings 1, 2

Table 2: Absolute Maximum Ratings

Symbol	Parameter	MIN	MAX	Units
V_{DD}	Positive Supply Voltage	-0.5	+7.2	V
V _I	Input Voltage	-0.5	V _{DD} +0.3	V
I _{CCC}	DC Channel Current		65	mA
P _D	Max Power Dissipation (3)		1.6	W
T _J	Junction Temperature		+150	°C
Θ _{JC}	Thermal resistance, junction-to-case		15	°C/W
T _{STG}	Storage Temperature	-65	+150	°C
ESD _{HBM}	ESD Protection (4)		2000	V

Notes:

- Stresses outside the listed absolute maximum ratings may cause permanent damage to the device. This is a stress rating
 only and functional operation of the device at these or any other conditions beyond limits indicated in the operational
 sections of this specification are not recommended. Exposure to absolute maximum rating conditions for extended periods
 may affect device reliability and performance.
- 2) All voltages referenced to V_{SS}
- 3) Per MIL-STD-883, method 1012, section 3.4.1, $P_D = (T_J(max) T_C(max))/\theta_{JC})$
- 4) Per MIL-STD-883, method 3015, Table 3

Operational Environment(1)

Table 3: Operational Environment

Symbol	Parameter	Limit	Units
TID	Total Ionizing Dose ⁽²⁾	300	krad(Si)
SEL	Single Event Latchup Immunity ⁽³⁾	≤100	MeV-cm ² /mg

Notes:

- 1) For devices with procured with a total ionizing dose tolerance guarantee, post-irradiation performance is guaranteed at 25°C per MIL-STD-883 Method 1019, Condition A up to maximum TID level procured.
- 2) Per MIL-STD-883, method 1019, condition A
- 3) SEL is performed at VDD = Max Voltage at 125°C

Recommended Operating Conditions(1)

Table 4: Recommended Operating Conditions

Symbol	Parameter	Conditions	MIN	MAX	Units
V_{DD}	Positive Supply Voltage		3.0 or 4.5	3.6 or 5.5	V
V_{IN}	Input Voltage on any pin		0.0	V_{DD}	V
T _C	Case Temperature Range		-55	+125	°C
t _R	Rise time, logic inputs	Transition from V_{IL} to V_{IH}		5	ns
t _F	Fall time, logic inputs	Transition from V_{IH} to V_{IL}		5	ns
I_{CCC}	DC Channel Current			60	mA

Note:



1) All voltages referenced to V_{SS}

DC Electrical Characteristics(1)

(V_{DD} = 5.0V \pm 0.5V, 3.3V \pm 0.3V, -55°C< Tc <+125°C); Unless otherwise noted, Tc is per the temperature range ordered

Table 5: DC Electrical Characteristics

Symbol	Parameter	Conditions	MIN	MAX	Units
V _{IH}	High digital input voltage	V _{DD} = 3.6, 5.5	0.7* V _{DD}		V
V _{IL}	Low digital input voltage	V _{DD} = 3.0, 4.5		0.3* V _{DD}	V
I_{ID}	Leakage current digital	V_{DD} (max); V_{I} = V_{DD} or V_{SS}	-1	1	μΑ
I_{IA}	Leakage current analog	V_{DD} (max); V_{I} = V_{DD} or V_{SS}	-1	1	μΑ
I_{DD}	Active supply current	V _{DD} = 3.6, 5.5		0.1	mA/MHz
I_{DDQ}	Quiescent Supply Current	V _{DD} (max); I _O =0mA; /EN=V _{DD}		15	μΑ
C _I	Input Capacitance (/EN) (2)	V _I =V _{DD} or V _{SS}		26	pF
C _{IO(OFF)}	Channel pin capacitance (channel disabled) (2)	V_{DD} (max); V_{O} = V_{DD} or V_{SS} ; V_{I} = $V_{DD}/2$; $/EN$ = V_{DD}		18	pF
		V _{DD} =4.5V, V _I =V _{SS} , /EN=0V, I _O =30mA		10	Ω
R _{ONL}	Resistance through switch	V_{DD} =4.5V, V_{I} = V_{SS} , /EN=0V, I_{O} =15mA		10	Ω
KONL	(channel input low) (3)	V_{DD} =3.0V, V_{I} = V_{SS} , /EN=0V, I_{O} =30mA		12	Ω
		V_{DD} =3.0V, V_{I} = V_{SS} , /EN=0V, I_{O} =15mA		12	Ω
		V _{DD} =4.5V, V _I =V _{DD} , /EN=0V, I _O =-30mA		10	Ω
D	Resistance through switch	V_{DD} =4.5V, V_{I} = V_{DD} , /EN=0V, I_{O} =-15mA		10	Ω
R _{ONH}	(channel input high) (3)	V _{DD} =3.0V, V _I =V _{DD} , /EN=0V, I _O =-30mA		12	Ω
		V_{DD} =3.0V, V_{I} = V_{DD} , /EN=0V, I_{O} =-15mA		12	Ω
		V_{DD} =4.5V, /EN=0V, I_{O} =+/-15mA, 25°C V_{IN} = V_{SS} , V_{DD} /2, V_{DD}		2	Ω
R _{ON(FLAT)}	Switch on resistance (3)	V_{DD} =3.0V, /EN=0V, I_{O} =+/-15mA, 25°C V_{IN} = V_{SS} , V_{DD} /2, V_{DD}		10	Ω

Notes:

- 1) All voltages referenced to V_{SS}
- 2) Per MIL-STD-883, method 3012
- 3) Guaranteed by Characterization



AC Electrical Characteristics¹

(V_{DD} = 5.0V \pm 0.5V, 3.3V \pm 0.3V, -55°C < Tc <+125°C); Unless otherwise noted, Tc is per the temperature range ordered

Table 6: AC Electrical Characteristics

Symbol	Parameter	Conditions	MIN	MAX	Units
t _{PD15}	Channel Propagation Delay (1)	V_{DD} = 5.0V ± 0.5V, I1=+/-15mA, /EN= V_{SS}		250	ps
t _{EN}	Channel Enable Delay (2)	$V_{DD} = 5.0V \pm 0.5V$	1	6	ns
t _{DIS}	Channel Disable Delay (2)	$V_{DD} = 5.0V \pm 0.5V$	1	6	ns
t _{PD15}	Channel Propagation Delay (1)	V_{DD} = 3.3V ± 0.3V, I1=+/-15mA, /EN= V_{SS}		250	ps
t _{EN}	Channel Enable Delay (2)	$V_{DD} = 3.3V \pm 0.3V$	1	8	ns
t _{DIS}	Channel Disable Delay (2)	$V_{DD} = 3.3V \pm 0.3V$	1	8	ns

Notes:

- 1) The propagation delay through the channel is based on the RC time constant of the channel capacitance and maximum channel resistance for defined V_{DD}
- 2) Measured at 300mV above or below steady state output voltage using output test load circuit

Table 7: Signal Characteristics

Symbol	Parameter	Conditions	MIN	TYP	MAX	Units
X _{TALK} ¹	Channel Cross-Talk (1,2)	V _{DD} = 5.0V			-60	dB
X _{TALK} ¹	Channel Cross-Talk (1,2)	$V_{DD} = 3.3V$			-60	dB
ISO _{OFF} ¹	Off Isolation (1,2)				-60	dB

Notes:

- 1) Guaranteed by design
- 2) RL = 50Ω , CL = 50pF, fin = 1MHz, Vin = 1VRMS centered at $V_{DD}/2$



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Timing Diagram



Figure 3: Channel Propagations Delay ($/EN = V_{SS}$)

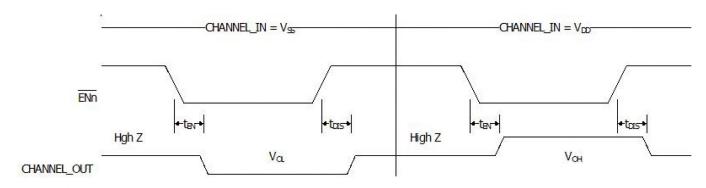


Figure 4: Enable Timing

Test Loads

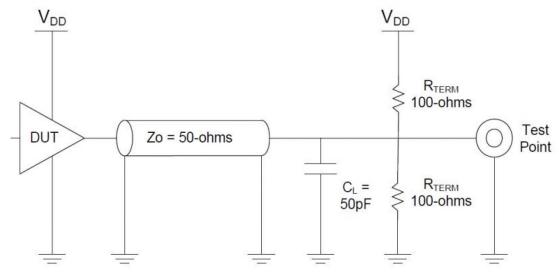


Figure 5. Standard Test Load



Package Drawings

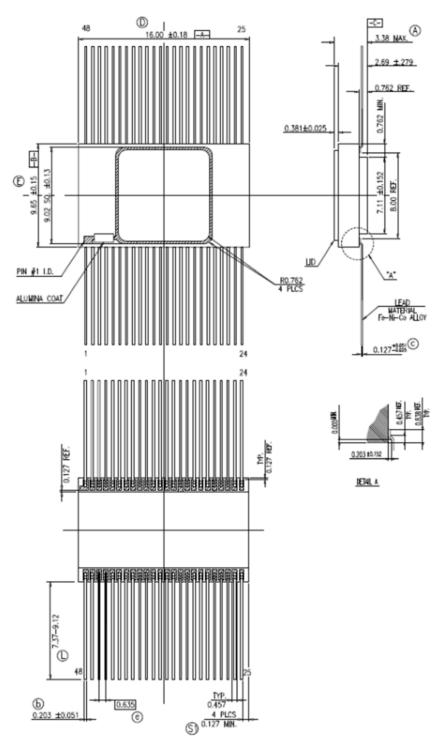


Figure 6: 48-Lead Flatpack

Notes:

1) Lid is connected to VSS.

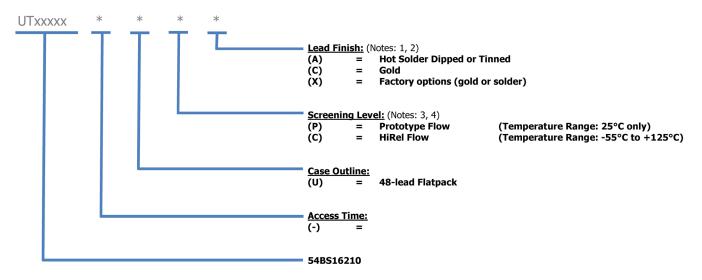


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2) Units are in millimeters.

Ordering Information

Generic Datasheet Part Numbering



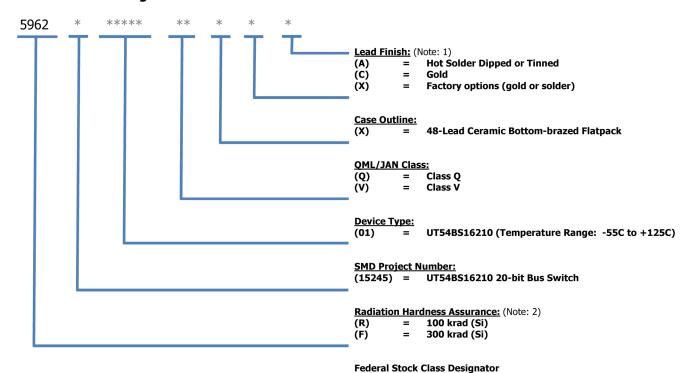
Notes:

- 1) Lead finish (A, C, F, or X) must be specified.
- 2) If an "X" is specified when ordering, then the part marking will match the lead finish applied to the device shipped
- 3) Prototype Flow per CAES Manufacturing Flows Document. Lead finish is Factory Option "C" only. Radiation is neither tested nor guaranteed.
- 4) HiRel Flow per CAES Manufacturing Flows Document. Radiation TID tolerance may (or may not) be ordered.



Ordering Information

SMD Part Numbering



Notes:

- 1) Lead finish must be specified. If "X" is specified when ordering, the factory will determine lead finish. Part marking will reflect the lead finish applied to the device shipped.
- 2) A radiation hardness assurance level must be selected. The use of "-" indicates no radiation hardness assurance guarantee.

Revision History

Table 8: Revision History

Date	Rev. #	Change Description	Initials
05/01/2016	1.0.0	Updated datasheet to reflect CAES logo, colors, and modified format. Updated the following specifications: R_{ON} , I_{IA} , I_{DD} , I_{DDQ} , T_{EN} , and T_{DIS} .	MM
06/23/2016	2.0.0	Released Datasheet. Updated capacitance and propagation delay. Minor formatting.	ВМ
06/27/2016	2.0.1	Package description correction, p.1: 48-Lead Flatpack	BM
6/30/2016	2.0.2	IDDQ: CONDITIONS: /EN=VDD	BM
01/04/2017	2.0.3	FEATURES: QML Q and V compliant part	BM
08/19/2021	2.0.5	ROC Table, p.4: Input t_R , t_F parameter updates.	BM



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Datasheet Definitions

DataSirect Definitions				
	DEFINITION			
Advanced Datasheet	CAES reserves the right to make changes to any products and services described herein at any time without notice. The product is still in the development stage and the datasheet is subject to change . Specifications can be TBD and the part package and pinout are not final .			
Preliminary Datasheet	CAES reserves the right to make changes to any products and services described herein at any time without notice. The product is in the characterization stage and prototypes are available.			
Datasheet	Product is in production and any changes to the product and services described herein will follow a formal customer notification process for form, fit or function changes.			

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